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T.S. 9/24/07

Amendments to the Specification

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9/24/07

Please replace the paragraph on page 3, line <sup>22</sup>~~18~~ with the following

amended paragraph:

The object is attained by using the recording film material for, as a phase change film of the nonvolatile memory, recording information by causing a reversible phase change between a crystal phase and an amorphous phase, the material including (1) a finite amount of at least one element selected from the group consisting of Ge and Sb, and (2) Te of 40 atom percent or more, and (3) at least one element selected from the elements in a 2b group, 1b group, 3a to 7a groups and an 8 group of 20 atom percent to 50 atom percent.